

T-27-09

## MAXIMUM RATINGS

Rating	Symbol	Value		Unit
		BCX17L BCX19L	BCX18L BCX20L	
Collector-Emitter Voltage	V <sub>CEO</sub>	45	25	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	50	30	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0		Vdc
Collector Current — Continuous	I <sub>C</sub>	500		mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	556	°C/W
Total Device Dissipation Alumina Substrate,** T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

\*FR-5 = 1.0 x 0.75 x 0.062 in.

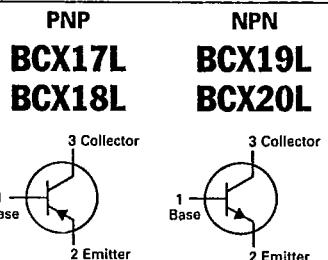
\*\*Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

## DEVICE MARKING

BCX17L = T1; BCX18L = T2; BCX19L = U1; BCX20L = U2

ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	45 25	—	—	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)CES</sub>	50 30	—	—	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	— —	— —	100 5.0	nAdc μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	—	—	10	μAdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 300 mAdc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 1.0 Vdc)	h <sub>FE</sub>	100 70 40	— — —	600	—
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)	V <sub>CE(sat)</sub>	—	—	0.62	Vdc
Base-Emitter On Voltage (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 1.0 Vdc)	V <sub>BE(on)</sub>	—	—	1.2	Vdc

CASE 318-03, STYLE 6  
SOT-23 (TO-236AB)GENERAL PURPOSE  
TRANSISTORS